

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-12 (Canceled).

Claim 13 (New): A method to produce conductive rods on an electronic component comprising one or more conductive blocks, each of the conductive rods being in at least partial contact with a block of the electronic component, the method comprising:

deposition of a conductive base on the component;

deposition of a masking layer on the conductive base;

formation in the masking layer of a plurality of holes, at least one conductive block of the conductive blocks being located opposite one or more holes;

filling of the holes with a conductive material base, by electrolysis and using the conductive base as an electrode, to form the conductive rods; and

removal of the masking layer.

Claim 14 (New): A method according to claim 13, wherein, in the formation in the masking layer of a plurality of holes, at least one conductive block of the conductive blocks is located opposite one or more holes, at least one hole of the holes has none of the conductive blocks opposite it, and the method further comprising, after the formation of the plurality of holes and prior to the filling by electrolysis:

etching the conductive base via the holes.

Claim 15 (New): A method according to claim 14, the masking layer comprising at least one photosensitive polymer layer.

Claim 16 (New): A method according to claim 14, wherein the conductive blocks are inserted in a passivation layer coating the electronic components.

Claim 17 (New): A method according to claim 14, the conductive base being formed from a stack of at least two different conductive layers.

Claim 18 (New): A method according to claim 14, further comprising, after the masking layer removal, an at least partial conductive base removal or selective conductive base etching.

Claim 19 (New): A method according to claim 14, further comprising, after the filling by electrolysis, an additional noble metal-based chemical deposition on the conductive rods.

Claim 20 (New): A microelectronic device obtained by the method according to claim 14.

Claim 21 (New): A method according to claim 13, wherein, in the formation in the masking layer of a plurality of holes, at least one conductive block of the conductive blocks is located opposite one or more holes, at least one hole of the holes has none of the conductive blocks opposite it, the method further comprising, between the deposition of the conductive base on the component and the deposition of the masking layer on the conductive base:

deposition of a thin insulating layer on the conductive base; and

formation of a plurality of openings in the thin insulating layer, each opening being located opposite a conductive block.

Claim 22 (New): A method according to claim 21, the masking layer comprising at least one photosensitive polymer layer.

Claim 23 (New): A method according to claim 21, wherein the conductive blocks are inserted in a passivation layer coating the electronic components.

Claim 24 (New): A method according to claim 21, the conductive base being formed from a stack of at least two different conductive layers.

Claim 25 (New): A method according to claim 21, further comprising, after the masking layer removal, an at least partial conductive base removal or selective conductive base etching.

Claim 26 (New): A method according to claim 21, further comprising, after the filling by electrolysis, an additional noble metal-based chemical deposition on the conductive rods.

Claim 27 (New): A microelectronic device obtained by the method according to claim 21.

Claim 28 (New): A method according to claim 21, wherein, of the plurality of holes formed in the hole formation in the masking layer, some holes reveal the thin insulating layer, and some other holes reveal the conductive base.

Claim 29 (New): A method according to claim 13, wherein, in the formation in the masking layer of a plurality of holes, each hole is at least partially located opposite a conductive block.

Claim 30 (New): A method according to claim 29, further comprising, after the formation in the masking layer of a plurality of holes and prior to the filling by electrolysis: etching of the conductive base via the holes.

Claim 31 (New): A method according to claim 29, the masking layer comprising at least one photosensitive polymer layer.

Claim 32 (New): A method according to claim 29, wherein the conductive blocks are inserted in a passivation layer coating the electronic components.

Claim 33 (New): A method according to claim 29, the conductive base being formed from a stack of at least two different conductive layers.

Claim 34 (New): A method according to claim 29, further comprising, after the masking layer removal, an at least partial conductive base removal or selective conductive base etching.

Claim 35 (New): A method according to claim 29, further comprising, after the filling by electrolysis, an additional noble metal-based chemical deposition on the conductive rods.

Claim 36 (New): A microelectronic device obtained by the method according to claim 29.